

Silicon Standard Recovery Diode

$V_{RRM} = 100\text{ V} - 1600\text{ V}$
 $I_F = 40\text{ A}$

Features

- High Surge Capability
- Types up to 1600 V V_{RRM}

DO-5 Package



Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	S40B (R)	S40D (R)	S40G (R)	S40J (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		100	200	400	600	V
RMS reverse voltage	V_{RMS}		70	140	280	420	V
DC blocking voltage	V_{DC}		100	200	400	600	V
Continuous forward current	I_F	$T_C \leq 140\text{ }^\circ\text{C}$	40	40	40	40	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$	595	595	595	595	A
Operating temperature	T_j		-65 to 190	-65 to 190	-65 to 190	-65 to 190	$^\circ\text{C}$
Storage temperature	T_{stg}		-65 to 190	-65 to 190	-65 to 190	-65 to 190	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	S40B (R)	S40D (R)	S40G (R)	S40J (R)	Unit
Diode forward voltage	V_F	$I_F = 40\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$	1.1	1.1	1.1	1.1	V
Reverse current	I_R	$V_R = 100\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$	10	10	10	10	μA
		$V_R = 100\text{ V}$, $T_j = 190\text{ }^\circ\text{C}$	15	15	15	9	mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		1.25	1.25	1.25	1.25	$^\circ\text{C/W}$
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Figure .1-Typical Forward Characteristics

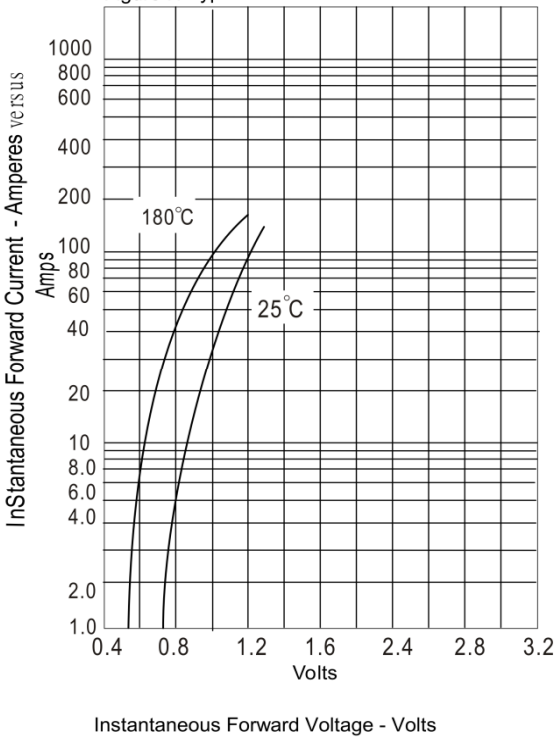


Figure .2- Forward Derating Curve

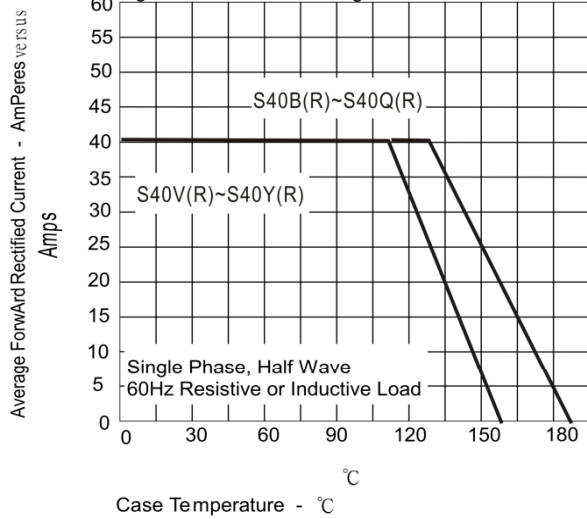


Figure .4-Typical Reverse Characteristics

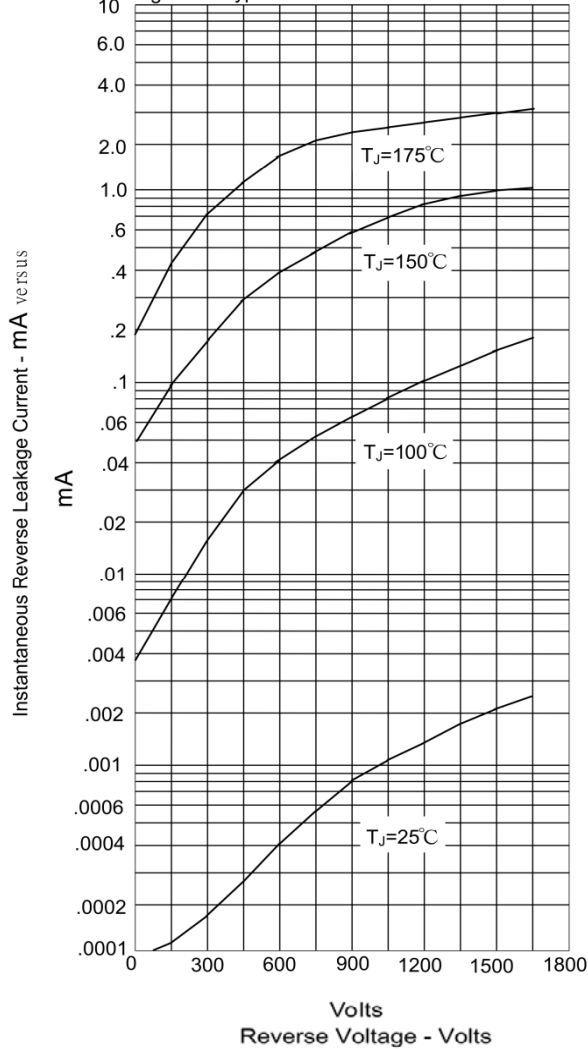


Figure .3-Peak Forward Surge Current

